Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	2	"6248383".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 13:47
L3	3	("3970520" | "4482574" | "4871575").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/28 13:46
L6	72266	(("702") or ("705")).CLAS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/28 15:47
L8	2	L6 and (yield with (ratio percentage)) same (process$3 with (material product)) same (raw with (material product))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 15:47
S1	136	zhang-xin$.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 14:04
S2	23320	fujitsu with limited$.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 14:04
S4	1	10/749550	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 14:29
S9	2	(S1 S2) and (yield with percentage) and (control$4 process$3) and ((updat$3 calibrat$3 correct$3) same (yield with percentage))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 14:34
S10	221	(yield with percentage) and (control$4 process$3) and ((updat$3 calibrat$3 correct$3) same (yield with percentage))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 14:34
S11	18	(yield with percentage) and (raw with material) and (control$4 process$3) and ((updat$3 calibrat$3 correct$3) same (yield with percentage))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 14:55

S12	16	(yield with percentage) and (raw with material) and (control$4 process$3) and ((updat$3 calibrat$3 correct$3) same (yield with percentage)) and ((K with value)weight)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 14:57
S17	21	(yield same percentage) and (raw with material) and (control$4 process$3) and ((record$3 updat$3 calibrat$3 correct$3) same yield same percentage) and (K weight) not S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/27 15:41
S18	14	(yield same percentage) and (control$4 process$3) and ((record$3 updat$3 calibrat$3 correct$3) same yield) and ((K with factor) same weight)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 07:01
S21	14	(yield same percentage) and (control$4 process$3) and ((record$3 updat$3 calibrat$3 correct$3) same yield) and ((K with factor) same weight)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 07:02
S24	326	((yield with (ratio percentage)) same (control$4 process$3) same (record$3 updat$3 calibrat$3 correct$3)) and ("K" weight)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 07:06
S25	67	(yield with (ratio percentage)) same (control$4 process$3) same (record$3 updat$3 calibrat$3 correct$3) same ("K" weight)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 07:06
S26	8	((yield with (ratio percentage)) same (control$4 process$3) same (record$3 updat$3 calibrat$3 correct$3) same ("K" weight)) and (raw with material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 09:02
S27	227	((yield same (ratio percentage)) same (control$4 process$3) same (record$3 updat$3 calibrat$3 correct$3) same ("K" weight)) not S26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 09:10
S28	59	((yield with(ratio percentage)) same (control$4 process$3) same (record$3 updat$3 calibrat$3 correct$3) same ("K" weight)) not S26	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 09:11
S32	1	sawazaki-hideki$.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 13:46

S33	6	((yield with(ratio percentage)) same (control$4 process$3) same (record$3 updat$3 calibrat$3 correct$3) same ("K" weight)) and processed and raw	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 09:31
S35	24	(yield same (ratio percentage) same manage$4) and ((processed raw)with material)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 10:11
S36	12	(percentage with raw with (material product) with produce with process$3 with (material product))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 10:23
S38	3730	(yield with (ratio percentage)) and (process$3 with (material product)) and (raw with (material product))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 10:25
S39	154	(yield with (ratio percentage)) same (process$3 with (material product)) same (raw with (material product))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 15:47
S40	4	(yield with (ratio percentage)) same (process$3 adj (material product)) same (raw adj (material product))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 10:26
S41	10	(yield with (ratio percentage)) same (process$3 near (material product)) same (raw near (material product))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 10:32
S42	41	(yield with (ratio percentage)) and ((process$3 adj (material product)) same (raw adj (material product)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 10:33
S43	8	(yield adj (ratio percentage)) and ((process$3 adj (material product)) same (raw adj (material product)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 15:47

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